

Silicon NPN Power Transistors

2SC2275 2SC2275A

DESCRIPTION

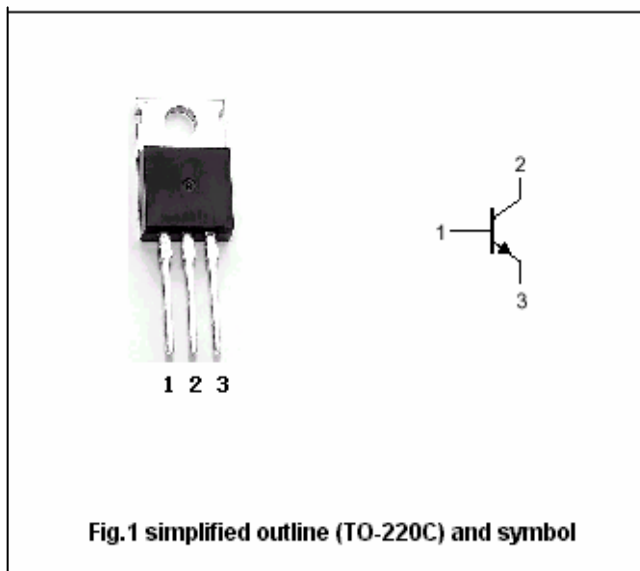
- With TO-220 package
- Complement to type 2SA985/985A
- High breakdown voltage

APPLICATIONS

- For low frequency and high frequency power amplifier applicatons

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SC2275	Open emitter	120	V
		2SC2275A		150	
V_{CEO}	Collector-emitter voltage	2SC2275	Open base	120	V
		2SC2275A		150	
V_{EBO}	Emitter-base voltage		Open collector	5	V
I_C	Collector current			1.5	A
I_{CM}	Collector current-peak			3.0	A
I_B	Base current			0.3	A
P_C	Collector power dissipation		$T_C=25$	25	W
T_j	Junction temperature			150	
T_{stg}	Storage temperature			-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SC2275	I _C =25mA, I _B =0	120			V
		2SC2275A		150			
V _{CEsat}	Collector-emitter saturation voltage		I _C =1A; I _B =0.1A			2.0	V
V _{BEsat}	Base-emitter saturation voltage		I _C =1A; I _B =0.1A			1.5	V
I _{CBO}	Collector cut-off current		V _{CB} =120V; I _E =0			1.0	μA
I _{EBO}	Emitter cut-off current		V _{EB} =3V; I _C =0			1.0	μA
h _{FE-1}	DC current gain		I _C =5mA; V _{CE} =5V	35			
h _{FE-2}	DC current gain		I _C =0.3A; V _{CE} =5V	60	150	320	
C _{OB}	Output capacitance		I _E =0; V _{CB} =10V, f=1MHz		19		pF
f _T	Transition frequency		I _C =0.2A; V _{CE} =5V		200		MHz

◆ h_{FE-2} Classifications

R	Q	P
60-120	100-200	160-320

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PACKAGE OUTLINE

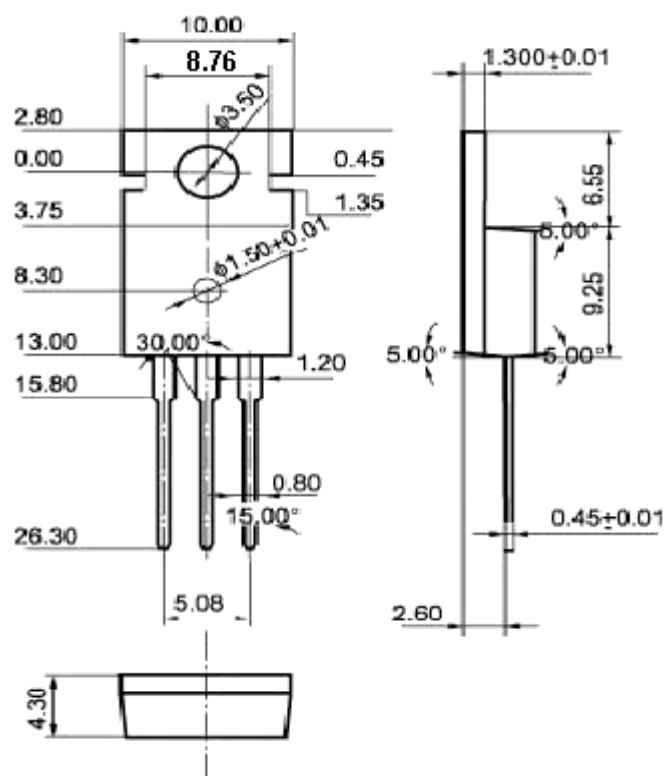


Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)